

09/ 943199



*Cope*  
*cc*

Docket No.: M4065.0704/P704  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:  
Kristy A. Campbell et al.

Patent No.: 6,955,940 *B2*

Issued: October 18, 2005

For: METHOD OF FORMING CHALCOGENIDE  
COMPRISING DEVICES

Certificate  
JAN 18 2006  
of Correction

REQUEST FOR CERTIFICATE OF CORRECTION  
PURSUANT TO 37 CFR 1.322 & 1.323

Attention: Certificate of Correction Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

In the Foreign Patent Documents portion of the References Cited Section, Applicants made the following error to be corrected:

"WO 97/488032" should read --WO 97/48032--.

In field (74) *Attorney, Agent, or Firm*, the PTO misspelled the name of the firm:

"Dickstein Shaprio Morin & Oshinsky LLP" should read --Dickstein Shapiro  
Morin & Oshinsky LLP--.

01/12/2006 SZWDIE1 00000047 6955940

01 FC:1811

100.00 DP

DSMDB.2026449.1

JAN 18 2006

In the Abstract, line 10, Applicants made the following error to be corrected:

"to and HNO<sub>3</sub>" should read --to an HNO<sub>3</sub>--.

In the Other Publications portion of the References Cited section, the PTO made the following errors:

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Also in the Other Publications portion of the References Cited section,  
Applicants made the following error to be corrected:

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In the Specification, Applicants made the following errors to be corrected:

Column 3, line 45, "example only, example" should read --example only,--;  
and

Column 6, line 52, "comprises and oxide" should read --comprises an oxide--.

In the Claims, the PTO made the following error to be corrected:

Claim 13, column 9, line 17, "atomosphere" should read --atmosphere--.

JAN 18 2008

The errors were made primarily by the PTO but were also found in the application as filed by applicant. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentees respectfully solicit the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0704/P704. A duplicate copy of this paper is enclosed.

Dated: January <sup>11</sup>~~10~~, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Peter McGee

Registration No.: 35,947

DICKSTEIN SHAPIRO MORIN &

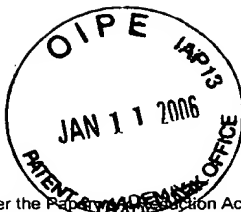
OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicants



PTO/SB/17 (12-04v2)  
Approved for use through 7/31/2006. OMB 0651-0032  
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE  
Under the Paperwork Reduction Act of 1995, no person are required to respond to a collection of information unless it displays a valid OMB control number.

<b>Effective on 12/08/2004.</b> <b>Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).</b>		<b>Complete if Known</b>	
<b>FEE TRANSMITTAL</b> <b>For FY 2005</b>		Application Number	Patent#: 6,955,940 <b>B2</b>
		Filing Date	Issued: October 18, 2005
		First Named Inventor	Kristy A. Campbell
		Examiner Name	D. Vu
		Art Unit	2818
<input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27		Attorney Docket No.	M4065.0704/P704
<b>TOTAL AMOUNT OF PAYMENT</b>		<b>(\$)</b>	<b>100.00</b>

<b>METHOD OF PAYMENT</b> (check all that apply)	
<input type="checkbox"/> Check	<input checked="" type="checkbox"/> Credit Card
<input type="checkbox"/> Money Order	<input type="checkbox"/> None
<input type="checkbox"/> Other (please identify):	
<input type="checkbox"/> Deposit Account	Deposit Account Number: <b>04-1073</b> Deposit Account Name: <b>Dickstein Shapiro Morin &amp; Oshinsky LLP</b>
For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)	
<input checked="" type="checkbox"/> Charge fee(s) indicated below	<input type="checkbox"/> Charge fee(s) indicated below, except for the filing fee
<input type="checkbox"/> Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17	<input checked="" type="checkbox"/> Credit any overpayments

<b>FEE CALCULATION</b>							
<b>1. BASIC FILING, SEARCH, AND EXAMINATION FEES</b>							
	<b>FILING FEES</b>		<b>SEARCH FEES</b>		<b>EXAMINATION FEES</b>		
		<b>Small Entity</b>		<b>Small Entity</b>		<b>Small Entity</b>	
<b>Application Type</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fee (\$)</b>	<b>Fees Paid (\$)</b>
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	
<b>2. EXCESS CLAIM FEES</b>							
						<b>Small Entity</b>	
						<b>Fee (\$)</b>	<b>Fee (\$)</b>
Each claim over 20 (including Reissues)						50	25
Each independent claim over 3 (including Reissues)						200	100
Multiple dependent claims						360	180
<b>Total Claims</b>		<b>Extra Claims</b>	<b>Fee (\$)</b>	<b>Fee Paid (\$)</b>	<b>Multiple Dependent Claims</b>		
_____		_____	x _____	= _____	<b>Fee (\$)</b>		<b>Fee Paid (\$)</b>
<b>Indep. Claims</b>		<b>Extra Claims</b>	<b>Fee (\$)</b>	<b>Fee Paid (\$)</b>			
_____		_____	x _____	= _____			
<b>3. APPLICATION SIZE FEE</b>							
If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).							
<b>Total Sheets</b>	<b>Extra Sheets</b>	<b>Number of each additional 50 or fraction thereof</b>			<b>Fee (\$)</b>	<b>Fee Paid (\$)</b>	
_____	_____	/50 _____ (round up to a whole number) x _____			= _____		
<b>4. OTHER FEE(S)</b>							
Non-English Specification, \$130 fee (no small entity discount)						<b>Fees Paid (\$)</b>	
Other (e.g., late filing surcharge): <b>1811 Certificate of correction</b>						<b>100.00</b>	

<b>SUBMITTED BY</b>			
Signature		Registration No. (Attorney/Agent)	28,371
Name (Print/Type)	Thomas J. D'Amico	Telephone	(202) 828-2232
		Date	January 18, 2006

JAN 18 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

Page 1 of 3

PATENT NO. : 6,955,940 *B2*  
APPLICATION NO. : 09/943,199  
ISSUE DATE : October 18, 2005  
INVENTOR(S) : Kristy A. Campbell et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

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MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico  
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 1  
2101 L Street NW  
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JAN 18 2006

"Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe<sub>2</sub> Crystals, Science 258 (1992) 271-274."

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